

SEMITOP[®] 3

3-phase bridge rectifier + brake chopper +3-phase bridge inverter **SK 8 DGDL 065 ET**

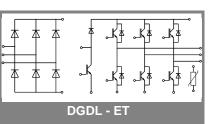
Target Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded alumium oxide ceramic (DCB)
- Ultrafast NPT technology IGBT
- CAL Technology FWD
- Integrated NTC temperature sensor

Typical Applications*

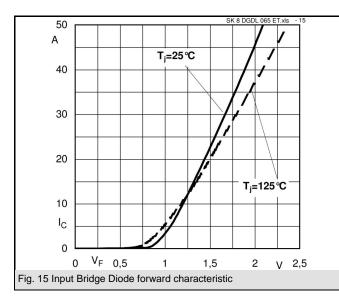
- Inverter
- Servo drives

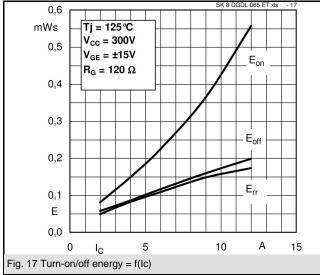


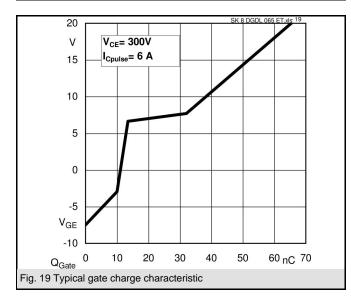
Absolute Maximum Ratings		T_s = 25°C, unless otherwise specified						
Symbol	Conditions	Values	Units					
IGBT - Inverter, Chopper								
V _{CES}		600	V					
I _C	T _s = 25 (80) °C	12 (8)	А					
I _{CRM}	I_{CRM} = 2 x I_{Cnom} , t_p = 1 ms	12	А					
V _{GES}		±20	V					
Т _ј		-40 +150	°C					
Diode - Inverter, Chopper								
I _F	T _s = 25 (80) °C	(13)	А					
I _{FRM}	I _{FRM} = 2xI _{Fnom} , t _p = 1 ms	16	А					
Т _ј		-40 +150	°C					
Rectifier								
V _{RRM}		1600	V					
I _D	T _s = 80 °C	33	Α					
I _{FSM} / I _{TSM}	t _p = 10 ms , sin 180 ° ,T _j = 25 °C		А					
l ² t	t _p = 10 ms , sin 180 ° ,T _j = 25 °C		A²s					
Т _ј		-40 +150	°C					
T _{sol}	Terminals, 10s	260	°C					
T _{stg}		-40 +125	°C					
V _{isol}	AC, 1 min. / 1s	2500 / 3000	V					

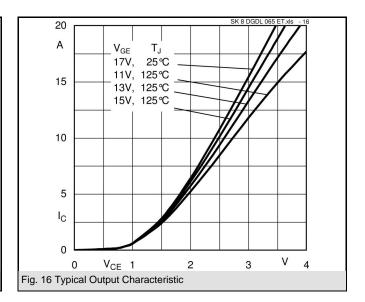
Characteristics		T _s = 25°C	T_s = 25°C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units	
IGBT - In	verter, Chopper	•				
V _{CEsat}	I _C = 6 A, T _i = 25 (125) °C		2 (2,2)		V	
V _{GE(th)}	$V_{GE} = V_{CE}, I_{C} = 0.5 \text{ mA}$	3	4	5	V	
V _{CE(TO)}	T _j = 25 °C (125) °C		1,2 (1,1)		V	
r _T	T _j = 25 °C (125) °C		133 (183)		mΩ	
C _{ies}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,35		nF	
C _{oes}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,04		nF	
C _{res}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,03		nF	
R _{th(j-s)}	per IGBT			2,6	K/W	
t _{d(on)}	under following conditions		20		ns	
t _r `́	V_{CC} = 300 V, V_{GE} = ± 15 V		25		ns	
t _{d(off)}	I _C = 6 A, T _j = 125 °C		145		ns	
t _f	$R_{Gon} = R_{Goff} = 120 \Omega$		25		ns	
Eon	inductive load		0,22		mJ	
E _{off}			0,12		mJ	
Diode - Ir	verter, Chopper					
V _F = V _{EC}	I _F = 8 Å, T _i = 25(125) °C	Ì	1,35		V	
V _(TO)	T _i = 25 °C (125) °C		(0,8)	(0,9)	V	
r _T	T _i = 25 °C (125) °C		(44)		mΩ	
R _{th(j-s)}	per diode			2,7	K/W	
I _{RRM}	under following conditions		4,2		Α	
Q _{rr}	I _F = 8 A, V _R = 300 V		0,65		μC	
Err	V _{GE} = 0 V, T _j = 125 °C				mJ	
	di _{F/dt} = -120 Å/µs					
Diode red	tifier	•				
V _F	I _F = 20 A, T _j = 25() °C		1,45		V	
V _(TO)	T _i = 125 °C		0,82		V	
r _T	T _i = 125 °C		35		mΩ	
R _{th(j-s)}	per diode			2,8	K/W	
	tur sensor					
R _{ts}	5 %, T _r = 25 (100) °C		5000(493)		Ω	
Mechanic	al data					
w			30		g	
Ms	Mounting torque	2,25		2,5	Nm	

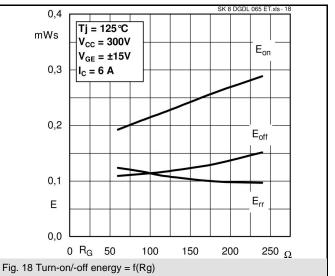
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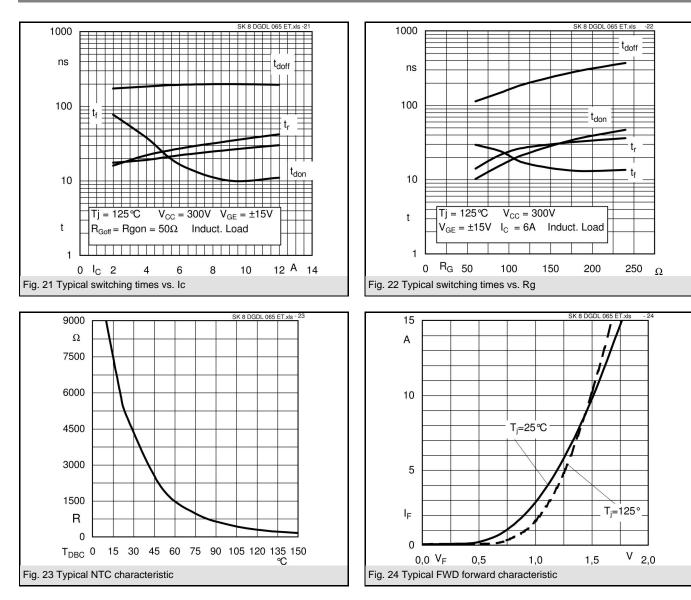




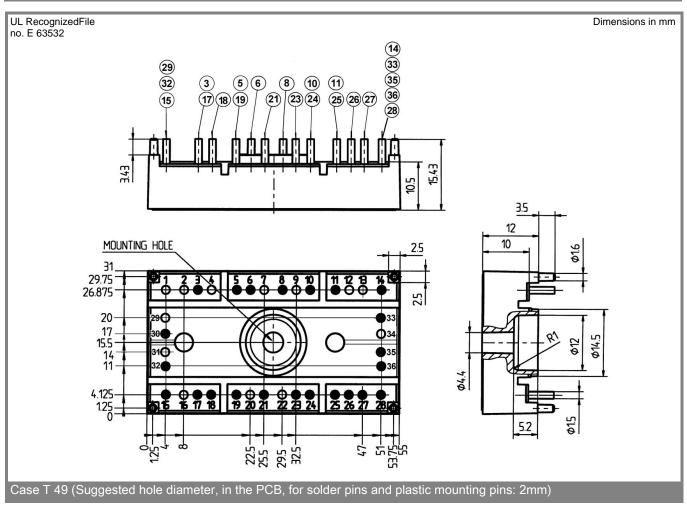


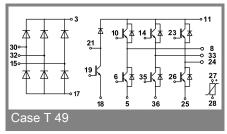






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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.